



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BVDSS	Rds(on)	I _D T _A = +25°C
20V	0.45Ω @ V _{GS} = 4.5V	0.87A
200	0.6Ω @ V _{GS} = 2.5V	0.76A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Load Switch
- **Power Management Functions**

Mechanical Data

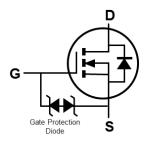
- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 63
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)



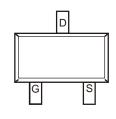
ESD PROTECTED



Top View



Equivalent Circuit



Top View

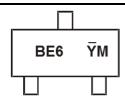
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2710UT-7	SOT523	3000/Tape & Reel
DMN2710UT-13	SOT523	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



BE6 = Product Type Marking Code YM = Date Code Marking \overline{Y} = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	Н	ı	J	K	L	М	N	0	Р	R	S	T
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Chai	racteristic		Symbol	Value	Unit
Drain-Source Voltage			VDSS	20	V
Gate-Source Voltage			V _{GSS}	±6	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	1A = 120 0			0.87 0.7	А
Maximum Continuous Body Diode Forward Current (Note 6)			Is	0.65	A
Pulsed Drain Current (10µs F	Pulse, Duty Cy	cle = 1%)	I _{DM}	5.6	A

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	0.32	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	395	°C/W
Total Power Dissipation (Note 6)		PD	0.52	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	241	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

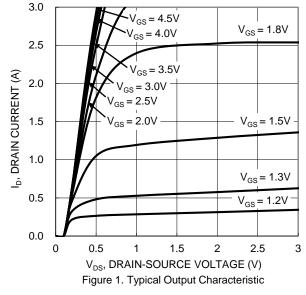
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

	1					
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BVDSS	20	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	100	nA	$V_{DS} = 20V$, $V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±1.0	μA	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	_	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
		_	0.14	0.45		$V_{GS} = 4.5V, I_{D} = 600mA$
Static Drain-Source On-Resistance	RDS(ON)	_	0.17	0.6	Ω	$V_{GS} = 2.5V, I_{D} = 500mA$
		_	0.22	0.75		V _G S = 1.8V, I _D = 350mA
Diode Forward Voltage	VsD	_	0.7	1.2	V	Vgs = 0V, Is = 150mA
DYNAMIC CHARACTERISTICS (Note 8)			•	•		
Input Capacitance	Ciss	_	42	_	pF	
Output Capacitance	Coss	_	13	_	pF	V _{DS} = 16V, V _{GS} = 0V - f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	6.5	_	pF	1 = 1.0WH1Z
Gate Resistance	Rg	_	1.6	_	kΩ	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge	Qg	_	0.6	_	nC	V 45V V 40V
Gate-Source Charge	Qgs	_	0.1	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $V_{DS} = 10V,$
Gate-Drain Charge	Q _{gd}	_	0.1	_	nC	ID = 250IIIA
Turn-On Delay Time	t _{D(ON)}	_	4.9	_	ns	
Turn-On Rise Time	t _R	_	3.1	_	ns	V _{DD} = 10V, V _{GS} = 4.5V,
Turn-Off Delay Time	t _D (OFF)	_	386	_	ns	$R_L = 47\Omega$, $R_g = 10\Omega$
Turn-Off Fall Time	tF	_	174	_	ns	I _D = 200mA
Reverse Recovery Time	t _{RR}	_	88	_	ns	I _F = 1.0A, di/dt = 100A/μs
Reverse Recovery Charge	Q_{RR}	_	29	_	nC	I _F = 1.0A, di/dt = 100A/μs

^{5.} Device mounted on FR-4 substrate PC board, with minimum recommended pad layout.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.7. Short duration pulse test used to minimize self-heating effect.

^{8.} Guaranteed by design. Not subject to product testing.





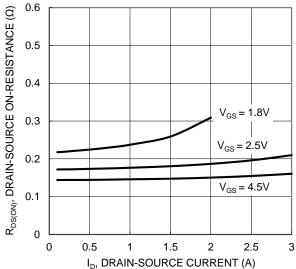


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

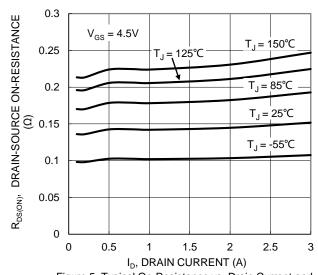
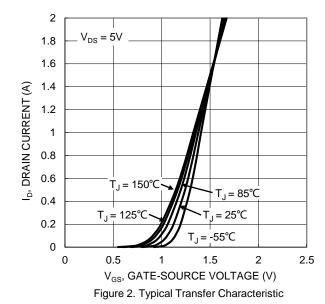
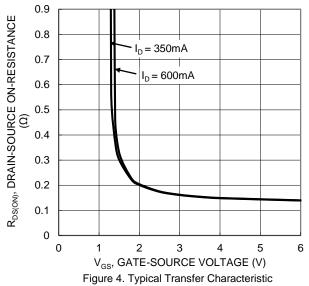


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





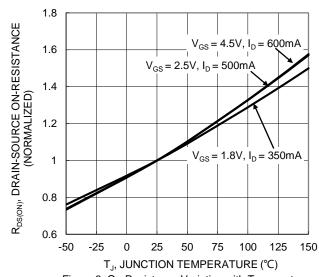


Figure 6. On-Resistance Variation with Temperature



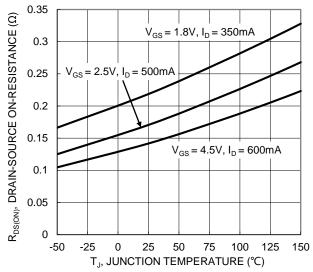


Figure 7. On-Resistance Variation with Temperature

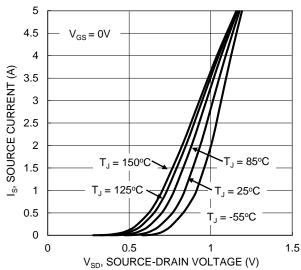


Figure 9. Diode Forward Voltage vs. Current

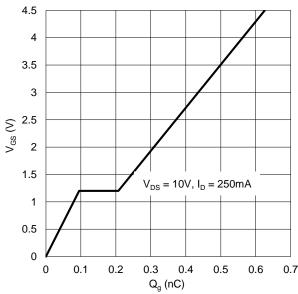


Figure 11. Gate Charge

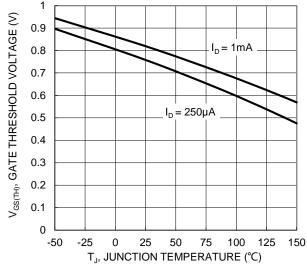
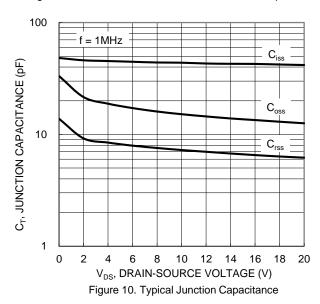


Figure 8. Gate Threshold Variation vs. Junction Temperature



10 $P_{W} = 100 \mu s$ ID, DRAIN CURRENT (A) = 1 ms $P_W = 10ms$ 0.1 $P_{W} = 100 \text{m}$ T_{J(Max)} = 150°C $P_W = 10s$ 0.01 T_C = 25℃ DC Single Pulse DUT on 1*MRP $V_{GS} = 4.5V$ 0.001 0.1 10 100 V_{DS} , DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



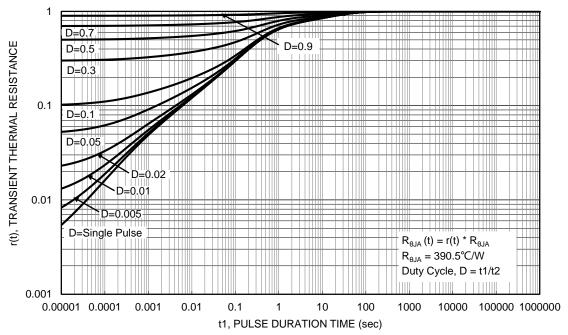


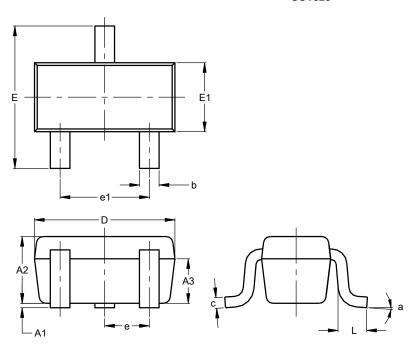
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523

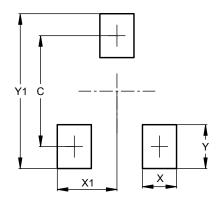


SOT523						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.60	0.80	0.75			
А3	0.45	0.65	0.50			
b	0.15	0.30	0.22			
С	0.10	0.20	0.12			
D	1.50	1.70	1.60			
Е	1.45	1.75	1.60			
E1	0.75	0.85	0.80			
е	0.50 BSC					
e1	0.90	1.10	1.00			
L	0.20	0.40	0.33			
а	0°		8°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523



Dimensions	Value (in mm)			
С	1.29			
Х	0.40			
X1	0.70			
Υ	0.51			
Y1	1.80			



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